

2N5060 THRU 2N5064

SILICON CONTROLLED RECTIFIERS
0.8 AMP, 30 THRU 200 VOLT



www.centrasemi.com

The CENTRAL SEMICONDUCTOR 2N5060 series devices are epoxy molded SCRs designed for control systems and sensing circuit applications.



TO-92 CASE

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N5060	2N5061	2N5062	2N5063	2N5064	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	30	60	100	150	200	V
RMS On-State Current (Note 1; $T_C=80^\circ\text{C}$)	$I_T(\text{RMS})$			0.8			A
Average On-State Current (Note 1; $T_C=67^\circ\text{C}$)	$I_T(\text{AV})$			0.51			A
Average On-State Current (Note 1; $T_C=102^\circ\text{C}$)	$I_T(\text{AV})$			0.255			A
Peak One Cycle Surge Current (60Hz)	I_{TSM}			10			A
I^2t Value for Fusing ($t=8.3\text{ms}$)	I^2t			0.4			A^2s
Peak Forward Gate Power ($t_p \leq 1.0\mu\text{s}$)	P_{GM}			0.1			W
Average Forward Gate Power ($t=8.3\text{ms}$)	$P_{G(\text{AV})}$			0.01			W
Peak Forward Gate Current ($t_p \leq 1.0\mu\text{s}$)	I_{GM}			1.0			A
Peak Reverse Gate Voltage ($t_p \leq 1.0\mu\text{s}$)	V_{RGM}			5.0			V
Operating Junction Temperature	T_J			-40 to +125			$^\circ\text{C}$
Storage Temperature	T_{stg}			-40 to +150			$^\circ\text{C}$
Thermal Resistance (Note 2)	θ_{JC}			75			$^\circ\text{C/W}$
Thermal Resistance	θ_{JA}			200			$^\circ\text{C/W}$

Notes: 1) 180° Conduction Angles

2) Measured with the "flat side down" on a heatsink and held in position by a metal clamp over the curved surface.

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	$V_D = \text{Rated } V_{DRM}, R_{GK} = 1.0\text{k}\Omega$			10	μA
I_{DRM}, I_{RRM}	$V_D = \text{Rated } V_{DRM}, R_{GK} = 1.0\text{k}\Omega, T_C = 110^\circ\text{C}$			50	μA
I_{GT}	$V_D = 7.0\text{V}, R_L = 100\Omega$			200	μA
I_{GT}	$V_D = 7.0\text{V}, R_L = 100\Omega, T_C = -40^\circ\text{C}$			350	μA
I_H	Initiating Current, $I_T = 20\text{mA}, R_{GK} = 1.0\text{k}\Omega$			5.0	mA
I_H	Initiating Current, $I_T = 20\text{mA}, R_{GK} = 1.0\text{k}\Omega, T_C = -40^\circ\text{C}$			10	mA
V_{GT}	$V_D = 7.0\text{V}, R_L = 100\Omega$			0.8	V
V_{GT}	$V_D = 7.0\text{V}, R_L = 100\Omega, T_C = -40^\circ\text{C}$			1.2	V
V_{GD}	$V_D = \text{Rated } V_{DRM}, R_L = 100\Omega, T_C = 110^\circ\text{C}$	0.1			V
V_{TM}	$I_{TM} = 1.2\text{A}, T_A = 25^\circ\text{C}$			1.7	V
dv/dt	$V_D = \text{Rated } V_{DRM}, R_{GK} = 1.0\text{k}\Omega$		30		$\text{V}/\mu\text{s}$

R5 (7-May 2015)

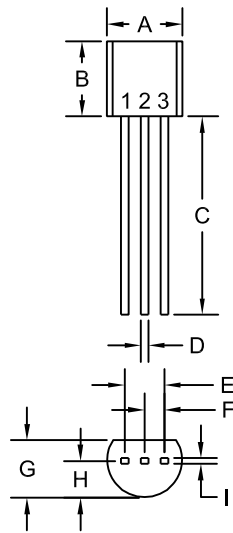
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ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5060	2N5062	UNITS
		2N5061	2N5063 2N5064	
		TYP	TYP	
t_d	[V_D =Rated V_{DRM} , $I_{GT}=1.0\text{mA}$, Forward Current=1.0A, $di/dt=6.0\text{A}/\mu\text{s}$]	3.0	3.0	μs
t_r		0.2	0.2	μs
t_q	[Forward Current=1.0A, $t_p=50\mu\text{s}$, 0.1% Duty Cycle, $di/dt=6.0\text{A}/\mu\text{s}$, $dv/dt=20\text{V}/\mu\text{s}$, $I_{GT}=1.0\text{mA}$]	10	30	μs

TO-92 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:

- 1) Cathode
- 2) Gate
- 3) Anode

MARKING:
FULL PART NUMBER

R1

R5 (7-May 2015)